# EBPG 5200+ Standard Operating Procedure

Version 1.0.1, Updated 5/7/2024

## QUICK GUIDE

### PROCEDURE OVERVIEW

- 1. Design
- 2. Conversion
- 3. Sample Loading
- 4. Prealignment
- 5. Job Creation
- 6. Job Scheduling
- 7. Unloading
- 8. Developing

## CRITICAL PRECAUTIONS AND COMMON MISTAKES

- The load lock door is a pinch point. Be cautious of your fingers when loading and unloading
- To keep pumpdown times low, keep the load lock door closed at all times
- Check that your sample is oriented correctly when you load it. Remember that the EBPG coordinate system is rotated from what you might expect.
- If you try to pattern within ~1mm of the edge of your sample, you will likely get a height sensor error. Height mapping (<u>Appendix A</u>) or sample redesign can resolve this.
- This SOP is written to ONLY provide some key operational procedures in a step-by-step

#### Tool condition for the next user

- •Pump the load lock with sample holders inside
- •Close all software windows except for cEBPG and cSYS
- •Make sure the illumination on the prealignment microscope is off and remote control is unselected in Calign
- Log out on NEMO

#### **MATERIALS RESTRICTIONS**

Needs to be vacuum compatible. Approved materials:

Only these Materials are Allowed	Restricted Materials (Staff permission req'd for each use)	Known Forbidden Materials
<ul> <li>Standard semiconductor and dielectric materials</li> <li>E-beam resists</li> <li>Low vapor pressure metals</li> </ul>	3 All other polymers	<ul> <li>Unbaked resist</li> <li>Outgassing materials</li> <li>Tape</li> <li>Silver Paste</li> </ul>

#### HANDLING REMINDERS

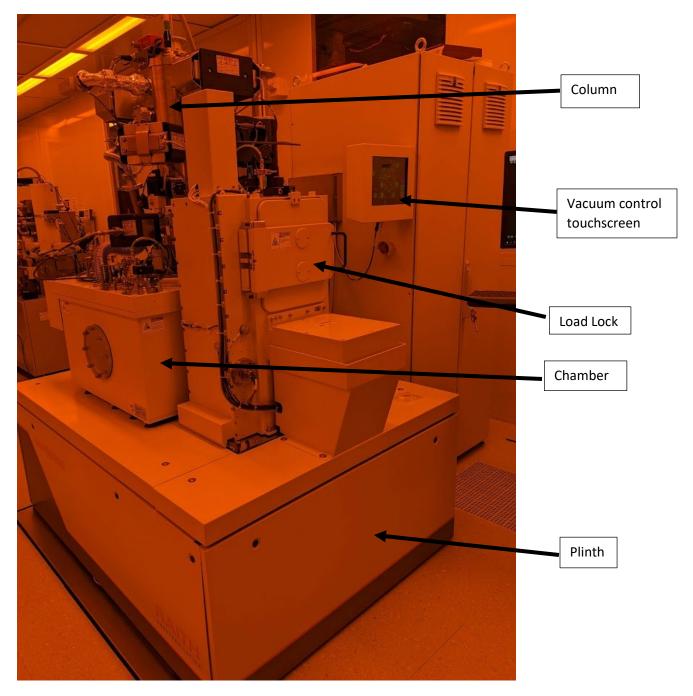
- Double glove when touching anything that enters the chamber
- Never touch or bump the reference samples affixed to the sample holders
- Soft tweezers are recommended
- Make sure back side of sample is clean
- Bake sample thoroughly to get rid of any solvents before writing
- Use the nitrogen gun to blow any particles off of the sample holder before loading

## **Tool Overview**

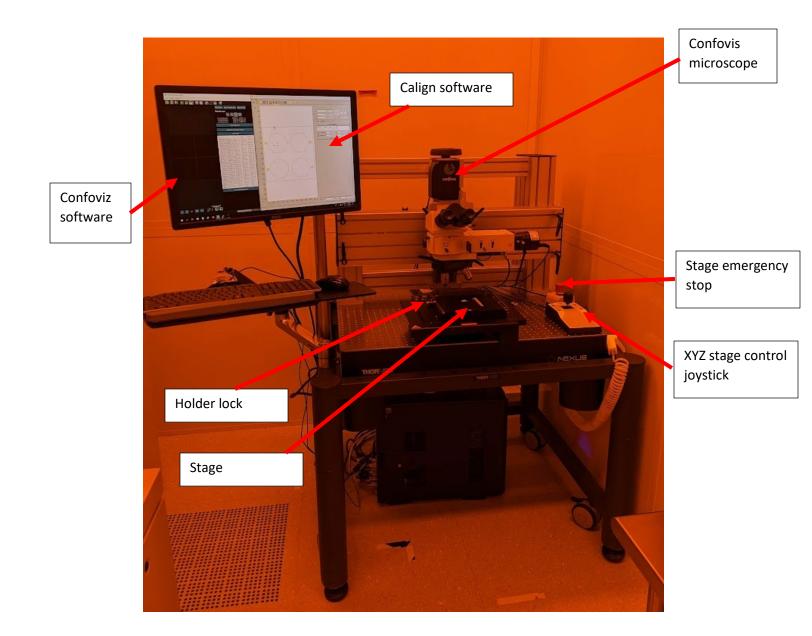
The EBPG 5200+ can be used for writing features with critical dimension down to ~8 nm over chips and wafers up to 200 mm in diameter. The accelerating voltage is 100 kV, and the beam current can be up to 350 nA. Overlay and stitching alignment accuracy of less than 10 nm can easily be achieved. The tool has automatic focus, stigmation, alignment, and beam and aperture switching. It has a 125 MHz pattern generator and 1.04 mm main field size.

#### **Hardware Overview**

EBPG 5200+ System

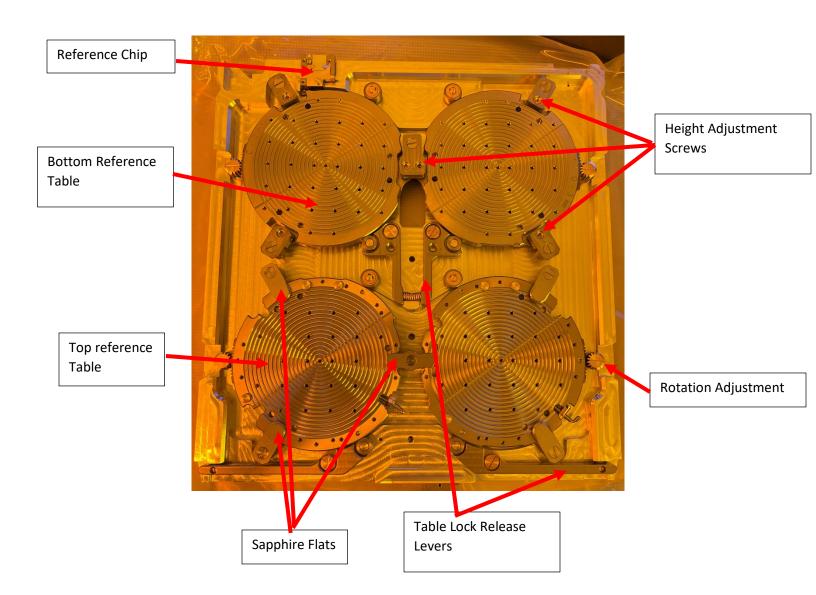


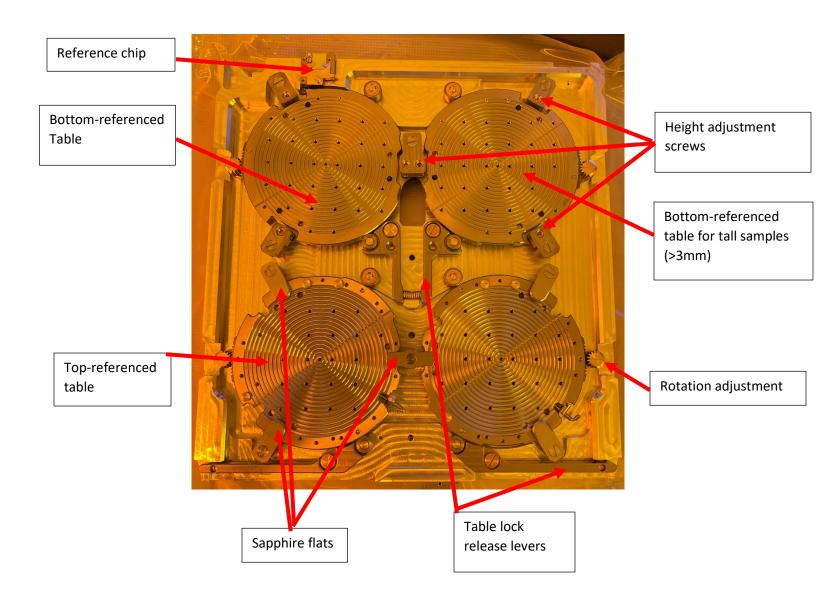
#### Prealignment Microscope



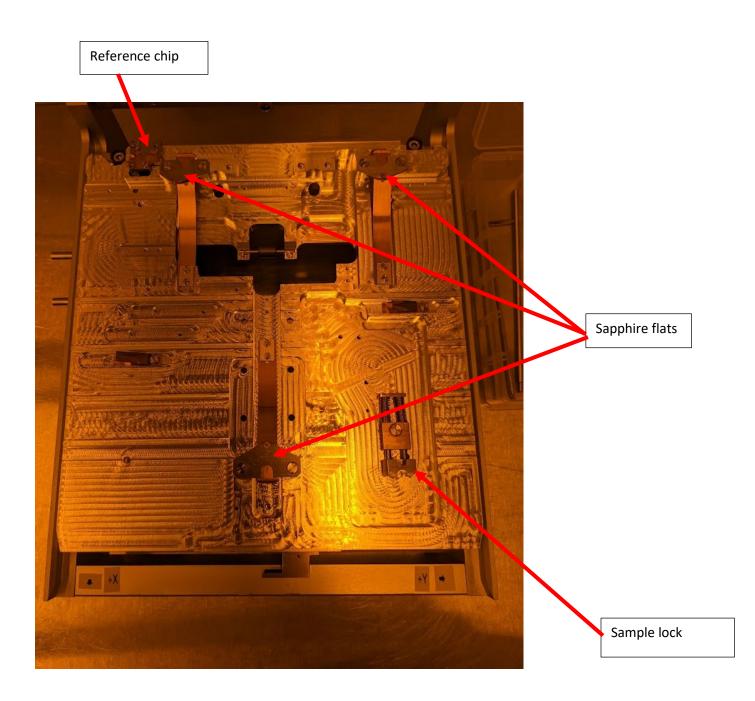
#### Sample Holders

0216 – 4x3" for piece parts – Slot 3

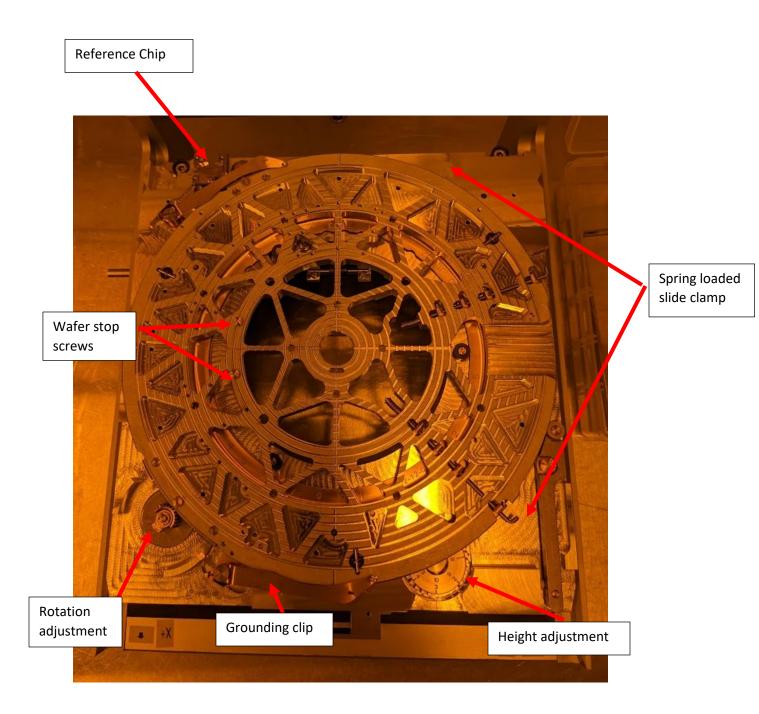




0088 – 6" mask holder – Slot 6



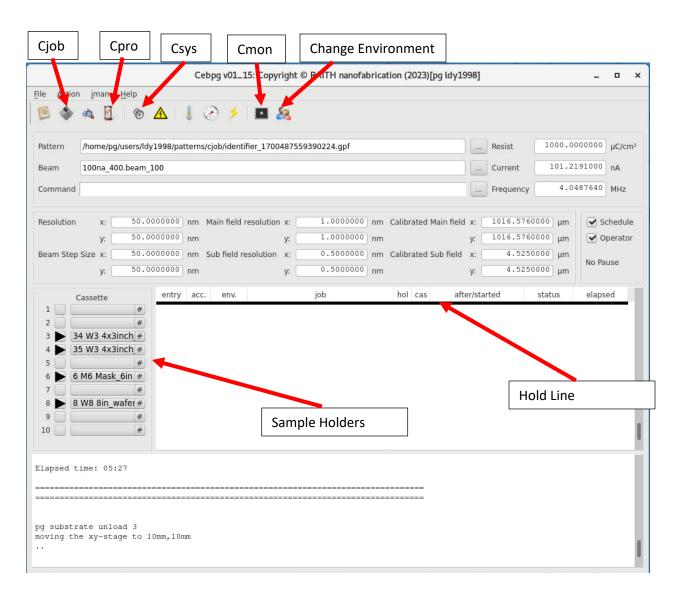
#### 0087 – Universal wafer holder, for 4",5",6",8" wafers – Slot 8



#### **Software Overview**

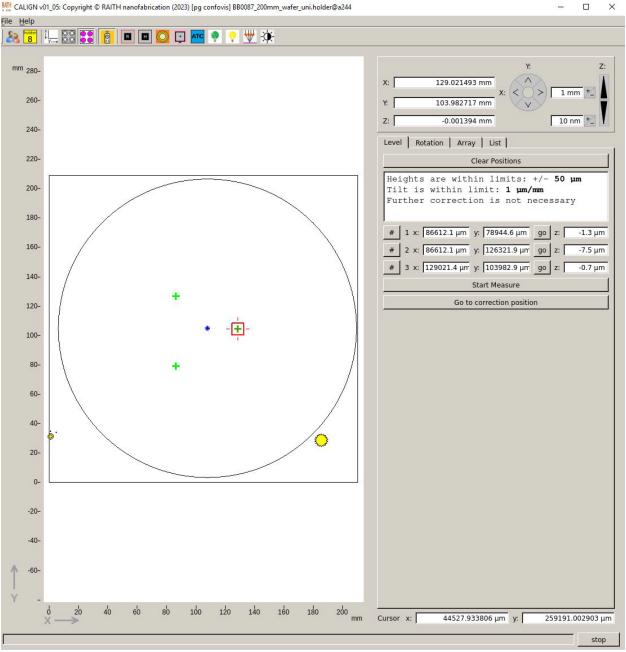
#### Cebpg

Cebpg is the main software to control the tool. It should always be open.



#### Calign

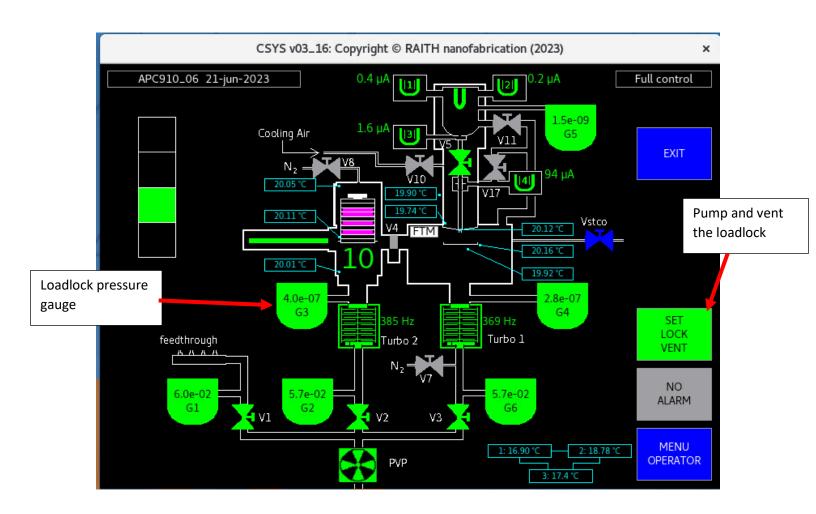
Calign is used on the prealignment microscope PC to measure and correct sample height, rotational alignment, and position



MI CALIGN v01\_05: Copyright © RAITH nanofabrication (2023) [pg confovis] BB0087\_200mm\_wafer\_uni.holder@a244

#### Csys

Csys should always be open. It shows an overview of the system, the vacuum status, and is where errors will appear. This is also displayed on the touchscreen, where the loadlock vacuum is controlled.



## **Full Procedure**

### Design

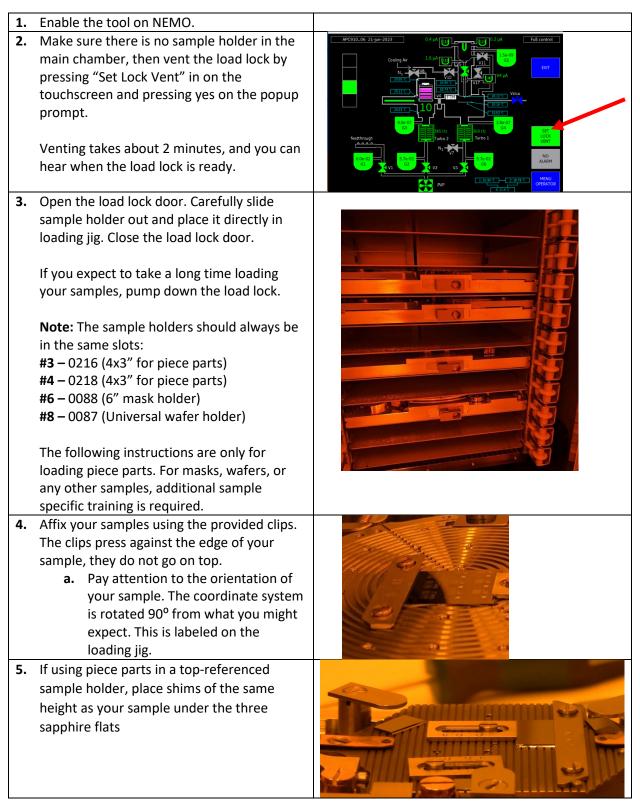
Layout files can be designed in your preferred software. LayoutEditor is provided and recommended. Designing your layout in GDS format is strongly recommended, though DXF and other formats are possible. In the EBPG, the origin will be in the center of your CAD, so designing it this way from the beginning can make things easier.

### Conversion

- 1. GDS files must be fractured and converted to the tool readable format [GPF]. This is done in beamer. A complete Beamer tutorial is beyond the scope of this SOP, but many resources are available.
- 2. Decisions made at this step in the lithography process are critical to the outcome. Proper pattern prep is among the most important parts of achieving the best possible results from your lithography. Take the time to do it right. The most important steps usually happen in the Beamer export module. A few important points about the export module are mentioned below.
  - a. The Beam Step Size (BSS, or shot pitch) must be chosen here. Generally, you should pick something 1/4 to 1/10 of your critical feature. Smaller BSS does not necessarily mean better writing.
  - b. Even though Beamer makes the resolution the same as the BSS by default, there is no reason for this. The resolution is effectively the pattern's design grid in the tool. Your BSS should always be a multiple of your resolution. There is generally no downside to setting the resolution to 1 nm. It can be set smaller, but this limits the maximum writing field size, so it should only be done if necessary.
  - c. The EBPG has a few unique fracturing and shot filling modes available in Beamer that drastically improve the fidelity of curves and circles, even with larger BSS

### Loading a Sample

Note: There is a training video about sample loading. Please watch it.



6.	Slide the sample holder out of the loading	
	jig and into the prealignment microscope	

## Prealignment

	angnment	
1.	Lock the sample holder in place in the prealignment microscope by pushing the lever on the right side of the stage back	
2.	In Calign, press the remote control icon to give the software control of the microscope. Then press the green light bulb to toggle the illumination on.	
3.	<ul> <li>Select sample holder</li> <li>a. Go to File -&gt; Open Holder</li> <li>b. Choose the holder you are using from the list</li> </ul>	
4.	<ul> <li>Find reference marker and set position</li> <li>a. Press the menu icon to drive to the reference marker. This should be the lower leftmost marker in the array</li> <li>b. Use the joystick to center crosshairs on marker</li> <li>c. Press ATC to adjust coordinates</li> </ul>	
5.	<ul> <li>Check your sample flatness</li> <li>a. Use joystick (with fast xy movement enabled) to drive to your sample</li> <li>b. Choose a point in the upper left of your sample. Once at that point, press the hash symbol for point 1 in the Level tab on Calign</li> </ul>	<ul> <li># 1 x: 86612.1 μm y: 78944.6 μm go z: -1.3 μm</li> <li># 2 x: 86612.1 μm y: 126321.9 μm go z: -7.5 μm</li> <li># 3 x: 129021.4 μm y: 103982.9 μm go z: -0.7 μm</li> <li>Start Measure</li> <li>Go to correction position</li> </ul>

	-	Depart for point 2 and 2 in the term with t	
	c.	Repeat for point 2 and 3 in the top right and bottom center of sample	
		respectively	
	d.	Once all points are defined, press 'Start	
	-	Measure'	
6.		a bottom-referenced table, the height	
		I flatness can be corrected by following	
		on-screen instructions	3
	а.	Go to the correction position	
	b.	Adjust each set screw by the amount	A
		shown on the display.	
	c.	Press the locking lever	-0.91
	d.	Remeasure flatness by pressing 'Start	0.11
		Measure' again.	C
7.	If u	sing a top-referenced table, usually	
	hei	ght will be in spec. If not:	
	a.	Make sure shims are in place (and the	
		right size)	
	b.	Make sure sample is sitting flat and	
		correctly clipped in place	
	c.	Make sure back side of sample is clean	
	d.	Remove shims and make sure they are	
		clean on front and back	
	e.	If none of these work, try a bottom-	
		referenced table	
8.	If o	verlay alignment is required, perform	
	rota	ation prealignment	Level Rotation Array List
	a.	The rotational alignment spec is 0.2° (=	Clear Positions
		3.5 μm/mm). Aligned writing cannot	Move stage to another marker, and
	_	proceed if rotation is out of spec.	Press GRAB (#) Second position
		Select the 'Rotation' tab in Calign	First x: 67911.8 µm y: 35855.8 µm go
	с.	Center microscope on first alignment	Second x: y: go
		mark and press the hash symbol next to 'First'.	correct positions
	d.	First . Drive to second mark (the two marks	
	u.	must be at the same x or y position in	
		your design). Press the hash symbol	The second se
	e.	Press 'Correct Positions'	• +X #
	f.	The software will instruct you to drive to	
		one of the mark positions. Use the 'go'	
		button next to the position	
	g.	The software will instruct you on turning	
	0	the rotation bolt. Follow the instructions	
		to use the rotation correction tool to	

	turn the bolt until the marker moves back to the center of the crosshairs	
9.	<ul> <li>Measure a reference position on your sample. For aligned writes, this is typically one known alignment mark. For unaligned writes, it is generally where you want the center of your pattern to be.</li> <li>a. Drive to desired position. Record X and Y coordinate from Calign software.</li> </ul>	X: 129.021493 mm Y: 103.982717 mm Z: -0.001394 mm
10.	<ul> <li>coordinate from Calign software.</li> <li>Load your sample into the tool</li> <li>a. Open the load lock door</li> <li>b. Unlock holder from microscope stage</li> <li>c. Slide holder into the correct spot in the load lock and close door</li> <li>d. Press "Set lock vacuum" on touchscreen</li> <li>e. Pumpdown usually takes ~5 minutes, depending on how long the loadlock was at atmospheric pressure</li> </ul>	
11.	Turn off the microscope illumination in Calign, and press the remote icon to turn off remote control	

#### **Job Creation**

1.	In Cebpg, press "Change Environment" and select your username from the list	File Action iman Help
2.	Move your gpf file from the shared folder to the "Patterns" folder in your directory. Shortcuts to the shared folder and the user directory on the EBPG PC are on the left desktop	
3.	Open Cjob	Cebpg v01_14: C
4.	<ul> <li>Build your job using the hierarchical structure and dragging blocks into the workspace. To place a block below one already in place, drag the new block from the left panel directly on top of the block in your workspace. Your cursor will change appearance to indicate that it is a valid placement.</li> <li>a. At minimum, a job requires a substrate, an exposure, and a pattern or shape</li> <li>b. Important features in each block are described below</li> </ul>	Cjob v02_19: Copyright © RAITH Elle View Options Windows 🖢 è Help Job Design substrate exposure layout patterm shape identifier
5.	Substrate The substrate defines the basic shape of your sample. It provides some visual cues about where your writing will occur, but it is not restrictive. You can write outside of the area defined here as your substrate. For convenience, it is recommended to get the dimensions approximately correct. The name field is required.	Select Substrate       Job       Machine Type: ebpg5150       Name       202102       Shift x: 0       y: 0       (µm),(µm)       Select mask size       *

#### Exposure

- 6. An exposure is a single file sent to the tool containing instructions on what and how to write. A single exposure can contain multiple patterns with different writing conditions (BSS, current, etc) as long as they are to be written at the same time. A job must have at least one exposure, and it can have multiple exposures (e.g. for the different steps of a multistep pattern).
  - a. The Pre Height Measure Layout selection is critical. It defines how the tool will manage the sample height during the exposure.
    - i. The default 'check' means that the tool will do a quick precheck of the expected write area. If any point in the precheck is either out of range or unmeasurable, the write will immediately fail. After the precheck, it will also check the height and adjust at every field in your pattern. If your sample is reflective and you are not writing within 1-2 mm of the edge of your chip, this is recommended.
    - ii. 'None' skips the precheck, but still checks the height at every field. By default, even if it cannot get a good measurement at a field, it will continue to write. This works when you are confident that the height is measurable in all critical areas, but the precheck might fail, for instance because the extents of your gpf file go off of your chip. If your height is out of spec, using this mode will result in very poor patterning.

Define Exposure					
Name: S5	Position: x: 0 y: 0				
High Tension 20kV 50kV • 100kV					
Working Level Stage <ul> <li>high</li> <li>low</li> </ul>					
Pre Height Measure Layout					
○ none ④ check ○ current map	O measure map				
Performance checks					
main field distortion errors     main field on-axis drift     current distribution over main field     beam quality over main field					
Init and Exit (ini + exi)					
Fixed Global Markers  Floating Global Markers					

i	ii.	'Current map' uses a predefined	
		height map, which is created	
		manually, and does not	
		measure the height at all. This is	
		used when the height is not	
		measurable everywhere you	
		need to write, but there are	
		measurable areas. The height at	
		the unmeasurable areas is	
		calculated by fitting the	
		measurable points to an	
		equation. This mode is	
		commonly used when patterns	
		(or markers) are very close to	
		the edge of the chip, where the	
		laser cannot measure. The	
		procedure for manually defining	
		a height map is in Appendix A.	
i	v.	'Measure map' is generally not	
		recommended. It will not fail	
		even when there are obvious	
		problems that ruin your	
	<i>(</i> <b>–</b>	patterning.	
b.		ixed global markers' are used to	
		efine markers for aligned writes.	
		ne procedure is covered in	
	A	ppendix B.	

#### Layout

Edit Layout 7. A layout is used to create an array of Positions [um. um] patterns, and can be used to perform Name: 4x4 0,0 <...> dose testing by varying the dose in Repetition 1 each element of the array. Layouts are Count Vector [µm] 4 # × 0 # y 0 # not required unless arraying of Spacing [µm] dx 100 dy 0 patterns is desired. Dropou Repetition 2 a. Count sets the number of <....> <....> Count Vector [µm] repetitions in each direction 4 # x 0 # y 0 # Spacing [µm] **b.** It is preferred to set the center to dx 0 dy 100 center spacing of the patterns with Scan Order dx and dy, not x and y Delete All serpentine Exception Except All c. Dose update can be done with an Circular ✓ Dose Update additive absolute dose, or with a Expression Plugin Upon multiplicative factor. Subtracting [µC/cm<sup>2</sup>] include Scan Order 
 Repetition 1
 Repetition 2 +- 0 or dividing is not recommended. Layout Markers Pattern Edit Pattern 8. Each pattern has a single gpf file and Pattern associated writing parameters. File Positions [µm, µm] vernier1.gpf 0,0 Multiple patterns with different <...> Resolution Main Res Sub Res BSS writing parameters can exist within a 0.001 0.001 0.0005 0.01 [µm] single exposure or layout. The position Beam Defocus [nm] field can be used to apply an offset to 10na\_300.beam\_100 ... 1 bin ff Dose [µC/cm²] Base Freq. the location of the pattern. This is 1500 6.66 [MHz] useful, but be cautious with it. Circular Pattern Markers Beam current and aperture are selected here. Keep in mind that beam parameters and BSS (chosen in Beamer) are closely interrelated, so these should already have been decided upon during the design phase. Patterns can be placed directly under exposures or within layouts in the job design.

Chana	Define Shape
<ul> <li>Shape</li> <li>9. Simple shapes (rectangles, crosses, and frames) can be defined directly in Cjob and do not require a CAD file to be converted in Beamer. This can be useful for marker arrays or other simple patterns. Resolution and BSS need to be specified here.</li> <li>Shapes are hierarchically equivalent to patterns.</li> </ul>	Shape         Size x [µm]         Feetangle         border         cross         2         pam         optimized         Resolution [µm]         Beam         Defocus         Beam         Defocus         ####         Circular         Shape Markers
Identifier	Identifier Type identifier Positions (um. um)
<ul> <li>10. clob can dynamically generate patterns with text and numbers to label your data. Most commonly, this is used to label a dose array with the dose of each element. It can also be use to add numbers to marker arrays or text labels. The insert button contains a list of commonly used identifiers.</li> <li>Identifiers fall below patterns hierarchically, so they should be placed under patterns in the job design.</li> </ul>	Type       identifier       Positions (µm, µm)         text       %q       Insert       0,-55         Font       Points       Style       Placement      >         helvetica       25       normal       center       line      >         Pixel width (µm)       Pixel height (µm)       Orientation      >      >         0,5       0.5       normal       invert      >         optimized       Beam       Defocus (nm)      >         0,05       0.05       0.05       0.05         Beam       Defocus (nm)       bin       ff         Dose (µC/cm²)       Base       Freq.       2000       1.61       [MHz]         Circular
11. Once job creation is finished and the preview accurately reflects the desired writing, the job should be exported. At this time, the software can also estimate the writing time for the job. Each exposure in the design is exported separately. A preview of the contents of each exposure can be seen on clicking the associated radio button.	step1         NO Pre-alignment           Reso         BSS         Main         Sub         Field         Defocus         Beam           1.000         5.000         1.000         0.500         1040.000         8na_300.beam_100           10.000         10.000         10.000         10.000         8na_300.beam_100           step2         NO Pre-alignment           Reso         BSS         Main         Sub         Field         Defocus         Beam           1.000         5.000         1.000         0.500         1040.000         8na_300.beam_100           50.000         50.000         10.000         0.500         1040.000         Bona_300.beam_100           full         NO Pre-alignment         Exposure Time         Export           File Name:         Exposure Time         Export           Jobs (*.job)         Help         Cancel

### Job Scheduling

	b Scheduling				
1.	Once the load lock is pumped down, you				
	can schedule and run your job				
2.	Make sure that the sample holders listed in the cassette in Cebpg accurately reflect the		Cassette		
	holder and cassette positions you are using.	1		(#)	
	If they do not match, click the name of the	2		#	
	holder and change it to the correct one. The	3	34 W3 4x3i	inch #	
	standard holders and locations are shown in	4	35 W3 4x3i	inch #	
	the picture here.	5		#	
		6	6 M6 Mask		
		7	O MO Mask_	(	
			0.11/0.01	#	
		8	8 W8 8in_w		
		9		#	
		10		#	
4.	holder in the schematic representation of the cassette in Cebpg. This loads your sample into the main chamber. Click the pound sign [#] next to that sample holder to bring up the job scheduling menu				
5.	Enter parameters for job:		Subr	mit Job: 869	×
5.	<b>a.</b> Select job file from list	Look in:			
	<ul> <li>b. Checking the no unload button is almost always recommended</li> <li>c. Set parameters. Usually the only parameter is to define the writing</li> </ul>		/home/pg/users/dbarth/jo		
			Name         Size         Type         Date Modified           20210315_grating_250nm         7 KB job File         3/15/21 11:21 AM           20210315 rects.job         4 KB job File         3/15/21 12:02 PM		
			15_rects.job 17 marks.job		/21 12:02 PM /21 3:25 PM
					holder 7 👻
	location. For unaligned writes, it will typically look as follows:	Parameters:	Grab Position	no unio	ad caspos 2 💌
	x_pos,y_pos	Log File:	/home/pg/users/dbarth/lo	g/0869log appe	nd
	Where: x_pos and y_pos are the x,y	Email:	dsbarth@gmail.com	atta	
	coordinates (in microns) copied from	After:		Filter: Jobs (*)	Cancel
	the prealignment microscope before			· · · · · · · · · · · · · · · · · · ·	
	loading. There should be a comma but				
	loauling. There should be a comma but				
	no space between the two coordinates.				
	no space between the two coordinates. A z coordinate can be used to use the z-				
	no space between the two coordinates. A z coordinate can be used to use the z- stage the offset the z position.				
6.	no space between the two coordinates. A z coordinate can be used to use the z- stage the offset the z position. Submit the job. It will now appear in the job				
6.	no space between the two coordinates. A z coordinate can be used to use the z- stage the offset the z position. Submit the job. It will now appear in the job queue in Cebpg with status 'HOLD.LINE'				
6. 7.	no space between the two coordinates. A z coordinate can be used to use the z- stage the offset the z position. Submit the job. It will now appear in the job	entry ac	c. env.		job

## Unloading your Sample

1.	When the job finishes, unload the sample	
	holder from the chamber, vent the load	
	lock, and unload your sample.	
2.	Refasten all clips, make sure all shims are	
	removed and tables are fully raised, load	
	sample holder back into load lock, and	
	pump down load lock.	
3.	Close all software except for Cebpg and Csys	
4.	Disable the tool in NEMO	

## Appendices

### **Appendix A: Manual Height Mapping**

When automatic height mapping and measurement cannot be used because of the specifics of a sample, manual mapping is required. This is usually done by using the laser height sensor to map height of the writing area and then using that to interpolate the height at each field. If, for example because of a transparent sample, the laser height sensor cannot be used at all, the tool can measure height by finding alignment marks at various offsets and make the height map by measuring multiple marks this way. Both procedures will be explained.

Successful application of either of these techniques require a good knowledge of the location and features of the sample when it is loaded into the tool. Make sure you understand your sample before it is in the tool, or you will likely have to take it out and try again.

Note: For terminal commands below, **Bold** text should be entered exactly as is, and *italicized* text indicates that a specific value needs to be substituted

1.	During job creation, in the exposure settings, select 'current map' as the Pre Height Measure Layout	Name:       exp       Position:       x:       0         High Tension       20kV       50kV       100kV         Working Level Stage       •       100kV         Working Level Stage       •       high       low         Pre Height Measure Layout       •       measure map
2.	Load the sample holder into the chamber	
	once load lock is pumped down	
3.	Open a terminal by right clicking on the	
	desktop and selecting 'open terminal'	
4.	Open the SEM control software, Cmon	
5.	Switch to your environment in the terminal	ce username
6.	Do initial stage calibration:	
	a. Find the sample holder marker	mvm
	<b>b.</b> Perform transform to adjust for	atc
	offset in marker location	
	<b>c.</b> Drive to faraday cup and measure	mcur
L_	current	
7.	Drive to reference position on your sample.	pg move pos x_pos,y_pos
	A known location such as an alignment	
	marker in the bottom left corner of your sample is preferred. The coordinates should	
	have been obtained from the prealignment	
	microscope, and they should be entered in	
	microns	
8.	If using the laser height sensor, attempt a	mpgm height
_	height measurement.	

<ul> <li>a. If the height cannot be measured at that position, usually this means that the position is too close to the edge of the sample. Use the step buttons in Cmon to move in towards the center of your sample, ~500 μm at a time, each time measuring the height as above. When you get a successful measurement, this is a good place to start your height map.</li> </ul>	Controls ♥ Operator Y: 10.295115 mm Y: 73.698163 mm Y: 73.698163 mm Contrast: 1.0 R Brightness: 0.0 R Frame Average: 1 ★ scans: 1
9. If using marker based height measurement, turn on the SEM image and find your first marker manually. When you are centered on the marker, turn off the SEM and have the tool do a marker search at the current location	mvmrel 0,0 markertype
<b>10.</b> When you have found a suitable location for the start of your height map using one of the two methods above, get the current stage position	mpg tab
11. Choose the size and spacing of points to measure in your height map. This depends entirely on your sample, but should encompass as much of the writing area as possible. For the marker method, each point must be at a marker on the sample	
<ul> <li>12. Run the height mapping command <ul> <li>a. For laser mapping:</li> <li>Where:</li> <li>i. start_x and start_y are the absolute stage coordinates in μm of the position to start the height map (determined in step 10)</li> <li>ii. step_x and step_y are the distance between measured points in μm</li> <li>iii. num_x and num_y are the number of points in the array in each direction</li> <li>iv. An order of 1 means that a linear fit is used on the measurements to interpolate the height. Other</li> </ul> </li> </ul>	<b>pg measure height arraymap</b> <i>start_x,start_y</i> <i>step_x,step_y num_x,num_y</i> <b>order=1</b>

orders can be used, but for small chips, a linear fit is usually best.	
Note: It is possible, and often more convenient to enter these values in mm instead of μm. This can be done by specifying the units in the command (e.g. 3mm,3mm instead of 3000,3000)	
<b>b.</b> For marker mapping:	<pre>pg measure height arraymap start_x,start_y step_x,step_y num_x,num_yorder=1marker=markertype</pre>
<b>13.</b> Check the height map. Make sure there are	pg info measure height map
no bad points and the numbers seem	
reasonable.	

## **Appendix B: Overlay Alignment**

Overlay alignment can be performed at all levels of the job hierarchy. If any overlay alignment is to be done, exposure level (global) alignment is required. All others are optional. Pattern level alignment is often used. Layout, shape, and identifier alignment is rare, but works the same way.

Note: For terminal commands below, **bold** text should be entered exactly as is, and *italicized* text indicates that a specific value needs to be substituted

1.	Define alignment marks in Cjob. Mark positions are in relative coordinates, so a thorough understanding of the coordinate system is necessary. The Cjob preview window is very helpful for this. If pattern level marks are being used, it is easier to define them first. Otherwise, skip to step 2 for exposure level marks.	
2.	Define exposure level marks	
3.	Define prealignment mark (optional but highly recommended)	
4.	Open a terminal window by right clicking on the desktop and selecting "open terminal"	
5.	Switch to your environment in the terminal	
6. 7.	<ul> <li>Do initial stage calibration:</li> <li>a. Find the sample holder marker</li> <li>b. Perform transform to adjust for offset in marker location</li> <li>Drive to faraday cup and measure current</li> </ul>	mvm atc mcur
8.	Drive to your first global marker (or your prealignment marker) using the coordinates recorded from the prealignment microscope.	pg move pos x_pos,y_pos

	Turn on SEM in Cmon and find your marker. Double click on the SEM image to position your beam directly over the marker If using automatic marker search, find the marker using the automatic search. If the markers cannot be found automatically by the tool, it can sometimes be possible to change the marker search settings to enable automatic mark finding. If you encounter this, discuss with staff. More often, the size is not correct or the sharpness at the edges is insufficient. In this case, manual mark finding must be used. The marker type in Cjob should be changed to 'manual'.	2021-06-153   Momrel 0,0 markertype	Controls ✓ Operator X: 10 Y: 73 Contrast: Brightness: Frame Averag Sem Image Sem on ⊙ sem on ⊙ single magnification pmhv
11.	Get the marker position	mpg tab	
12.	If prealignment marker is not used, repeat steps 8-11 for each global marker		
13.	Schedule the job. The position of the prealignment mark (or all global marks in order) should go in the parameters section.		
14.	Run the job. For automatic mark finding, no further input is necessary		

- **15.** For manual mark finding, a prompt will appear in the info area at the bottom of Cebpg. Follow the prompt:
  - a. Turn on the SEM. The marker should be in or near the field of view.
  - Use SEM crosshairs and the 'move to crosshairs' button in Cmon to center the marker.
    - Instead of the crosshairs, the 'mark' overlay can also be used. Right clicking allows different defined marks to be selected
  - c. Turn off the SEM
  - **d.** Click on the bottom line in Cebpg, where the prompt is, and press enter.
  - e. Repeat for each mark. If any mark cannot be seen, the job should be cancelled. Depending on the mark material, it can be necessary to adjust the brightness, contrast, and PMHV

■■ <b>= <del>-</del> + オ⊠ <b>≥</b> </b>	Controls
12 µm	Operator
10 µm	X: 1
8 µm	Y: 7
6 µm	Contrast:
4 µm	Brightness:
2 µm	Frame Avera
12 µm -10 µm -8 µm -6 µm -4 µm -2 µm 2 µm 4 µm 6 µm 8 µm 10 µm 12 µm	Sem Image
-2 μm	🔘 sem off
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-8 µт	magnincatio
-10 µm.	
2021-06-15 16:51:26	pmhv

### **Appendix C: Cold Development**

Cold development can improve resolution, contrast, and line edge roughness of positive resists (especially PMMA and ZEP) at the expense of sensitivity. A cold development tank is set up in the Nano-Process hood for this purpose. This consists of a thermoelectric cold plate with an aluminum bead bath on top of it. The cold plate is set at  $-10^{\circ}$  C. To develop using the cold tank, the development solution should be prepared in a beaker about 10 minutes in advance of development. The beaker should then be placed into the bead bath, making sure the beads cover the solution, and left to cool.

Note: do not leave the bead bath uncovered for more than a few minutes, as condensation can contaminate your development solution and make the bead bath difficult to use.

Once the developer solution is cool, place your sample in the solution for the desired amount of time (usually 30 to 120 seconds) remove the sample and rinse into a second beaker (usually with IPA). All liquid waste from this process should be poured into the solvent carboy cupsink in the Nano-Process hood.

Note: MIBK-IPA is no longer considered the standard recommended developer for PMMA. IPA:Water (3:1) gives superior contrast, resolution, and line edge roughness and is now considered the standard.

#### Version history

Draft	Date	Author	Notes on changes
v.1.0.0	11/22/2023	David Barth	First Draft
v.1.0.1	5/7/2024	David Barth	Minor Corrections